

Product Features

- 2.3 – 2.9 GHz
- +39 dBm P1dB
- 13.8 dB Gain
- 1.4% EVM @ 30 dBm Pout
- +12 V Supply Voltage
- Lead-free/green/RoHS-compliant 5x6 mm power DFN package

Applications

- WiMAX CPE/BTS
- WiBro CPE/BTS

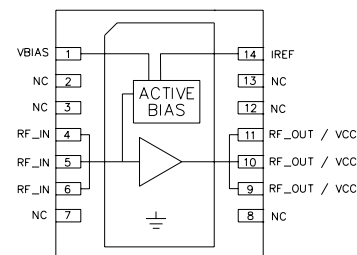
Product Description

The AP561 is a high dynamic range broadband power amplifier in a surface mount package. The single-stage amplifier has 13.8 dB gain, while being able to achieve high performance for 2.3–2.9 GHz WiMAX applications with up to 39 dBm of compressed 1dB power.

The AP561 uses a high reliability +12V InGaP/GaAs HBT process technology. The device incorporates proprietary bias circuitry to compensate for variations in linearity and current draw over temperature. The device does not require any negative bias voltage; an internal active bias allows the AP561 to operate directly off a commonly used +12V supply and has the added feature of a +5V power down control pin. RoHS-compliant 5x6mm DFN package is surface mountable to allow for low manufacturing costs to the end user.

The AP561 is targeted for use in a balanced or single ended configuration for WiMAX or WiBro applications where high linearity and high power is required.

Functional Diagram



Function	Pin No.
RF _{IN}	4,5,6
RF _{OUT}	9,10,11
I _{REF}	14
V _{BIAS}	1
NC	2,3,7,8,12,13

Specifications

Parameter	Units	Min	Typ	Max
Operational Bandwidth	GHz	2.3		2.9
Test Frequency	GHz		2.6	
Output Channel Power	dBm		+30	
Power Gain	dB		13.8	
Input Return Loss	dB		11	
Output Return Loss	dB		6.9	
Error Vector Magnitude	%		1.4	
Operating Current, I _{cc}	mA		480	
Collector Efficiency	%		16.8	
RF Switching Speed	ns		50	
Output P1dB	dBm		39	
Quiescent Current, I _q	mA		300	
V _{pd} ⁽⁴⁾	V		+5	
V _{cc}	V		+12	

Notes:

1. Test conditions unless otherwise noted: T = 25°C, V_{pd} = +5V, V_{cc} = +12, I_q = 300mA at P_{out} = +30 dBm and f = 2.6 GHz.
2. Using an 802.16-2004 OFDMA, 64QAM-1/2, 1024-FFT, 20 symbols, 30 subchannels signal, 9.5 dB PAR @ 0.01%.
3. Switching speed: 50% TTL to 100/0% RF.
4. V_{pd} used for device power down. (low=RF off)
5. Capable of handling 10:1 VSWR @ 12 V_{DC}, WiMax signal, P_{out,AVG} = 30dBm.

Typical Performance

Parameter	Units	Typical		
Test Frequency	GHz	2.5	2.6	2.7
Channel Power	dBm	+30	+30	+30
Power Gain	dB	14	13.8	13.5
Input Return Loss	dB	11	11	14
Output Return Loss	dB	6.2	6.9	5.7
Error Vector Magnitude	%	2.2	1.4	2.1
Operating Current, I _{cc}	mA	510	480	490
Collector Efficiency	%	15.8	16.8	16
Output P1dB	dBm	40	39	38
Quiescent Current, I _q	mA	300		
V _{pd}	V	+5		
V _{cc}	V	+12		

Absolute Maximum Rating

Parameter	Rating
Pin max (CW into 50Ω load)	+33 dBm
Storage Temperature	-55 to +125 °C
Max Junction Temperature, T _{J,max}	158 °C
Thermal Resistance, Θ _{JC}	8.4 °C / W

Operation of this device above any of these parameters may cause permanent damage.

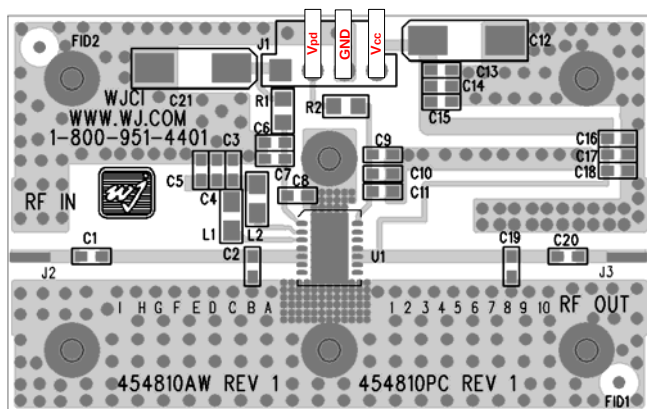
Ordering Information

Part No.	Description
AP561-F	WiMAX 12V 8W HBT Amplifier
AP561-PCB2500	2.5-2.7 GHz Fully Assembled Evaluation Board

Standard T/R size = 500 pieces on a 7" reel.

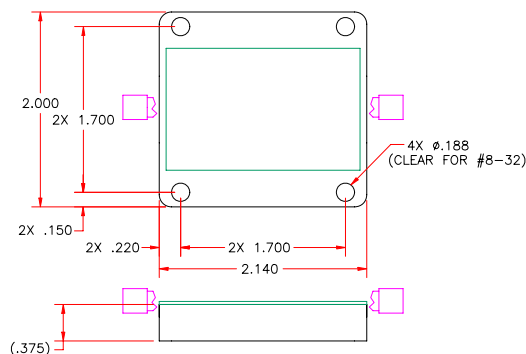
Specifications and information are subject to change without notice

Application Circuit PC Board Layout



Circuit Board Material: 0.0147" Rogers Ultralam 2000, single layer, 1 oz copper, $\epsilon_r = 2.45$, Microstrip line details: width = .042", spacing = .050"

Baseplate Configuration



Notes:

1. Please note that for reliable operation, the evaluation board will have to be mounted to a much larger heat sink during operation and in laboratory environments to dissipate the power consumed by the device. The use of a convection fan is also recommended in laboratory environments.
2. The area around the module underneath the PCB should not contain any soldermask in order to maintain good RF grounding.
3. For proper and safe operation in the laboratory, the power-on sequencing is recommended.

Evaluation Board Bias Procedure

Following bias procedure is recommended to ensure proper functionality of AP561 in a laboratory environment. The sequencing is not required in the final system application.

Bias.	Voltage (V)
Vcc	+12
Vpd	+5

Turn-on Sequence:

1. Attach input and output loads onto the evaluation board.
2. Turn on power supply Vcc = +12V.
3. Turn on power supply Vpd = +5V.
4. Turn on RF power.

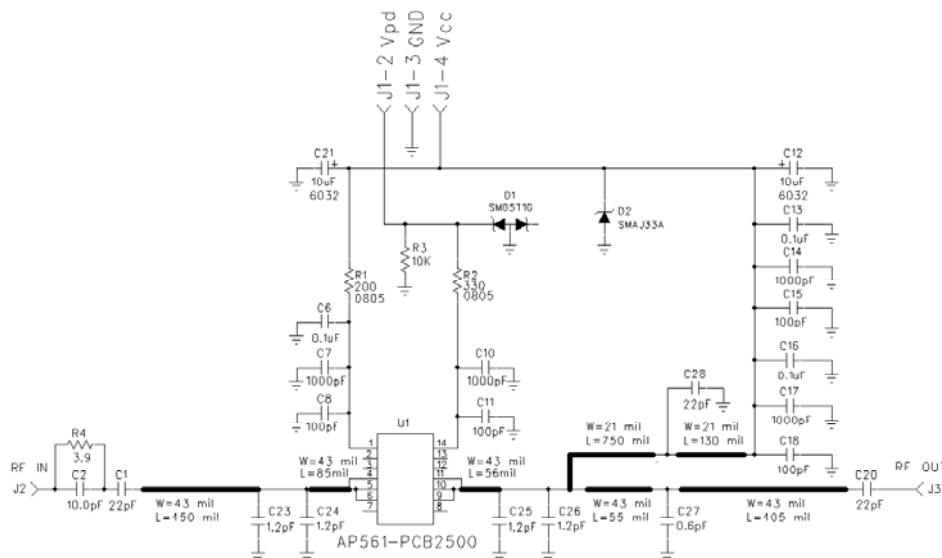
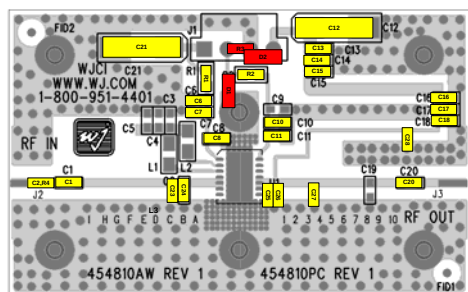
Turn-off Sequence:

1. Turn off RF power.
2. Turn off power supply Vpd = +5V.
3. Turn off power supply Vcc = +12V.

2.5-2.7 GHz Application Circuit (AP561-PCB2500)

Typical O-FDMA Performance at 25°C

Frequency (GHz)	2.5	2.6	2.7	Units
Channel Power	+30	+30	+30	dBm
Power Gain	14	13.8	13.5	dB
Input Return Loss	11	11	14	dB
Output Return Loss	6.2	6.9	5.7	dB
EVM	2.2	1.4	2.1	%
Operating Current, I _{cc}	510	480	490	mA
Collector Efficiency	15.8	16.8	16	%
Output P _{1dB}	40	39	38	dBm
Quiescent Current, I _{cq}	300			mA
V _{pd}	+5			V
V _{cc}	+12			V



Notes:

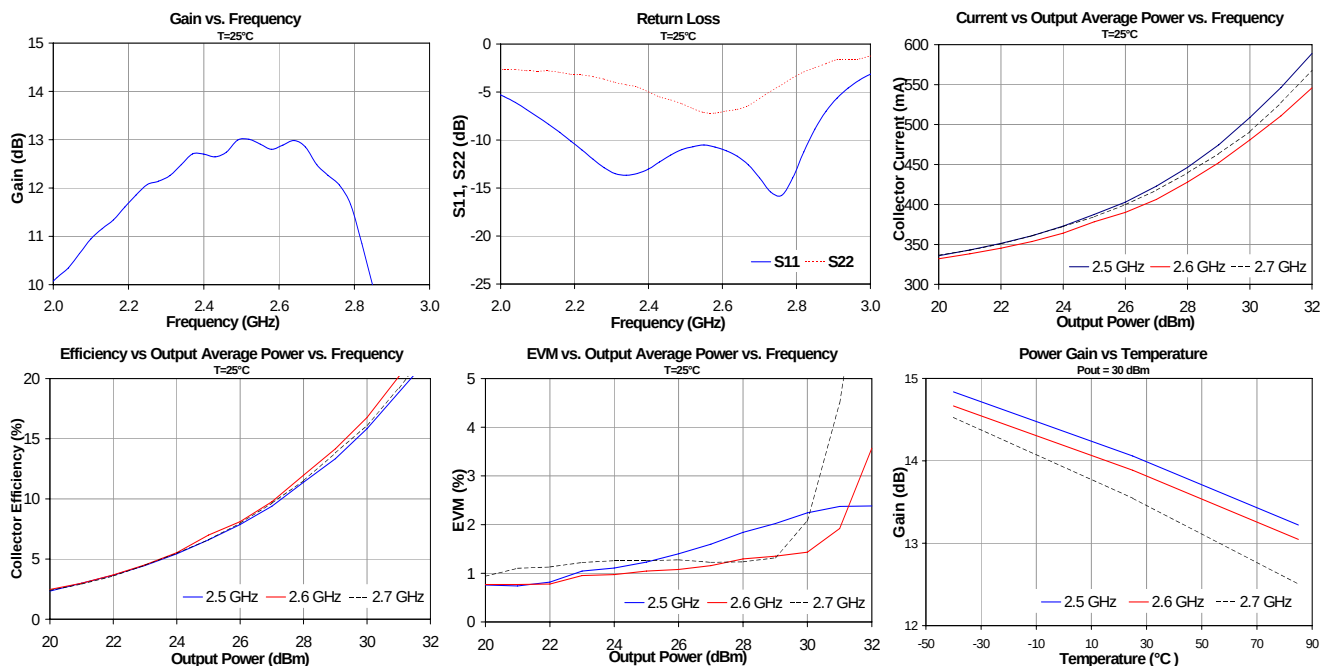
The primary RF microstrip line is 50 Ω.

Components shown on the silkscreen but not on the schematic are not used.

1. The edge of C23 is placed right next to C24.
2. The edge of C24 is placed at 85mil from AP561 RFout pin.
3. The edge of C25 is placed at 56mil from AP561 RFin pin.
4. The edge of C26 is placed right next to C25.
5. The edge of C27 is placed 55mil from the edge of C26.

2.5-2.7 GHz Application Circuit Performance Plots

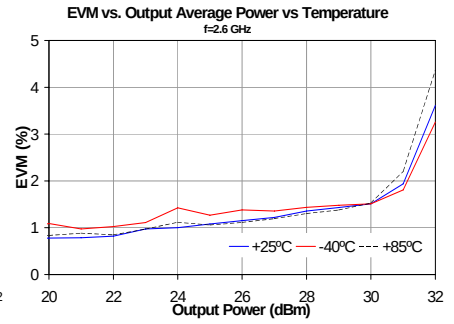
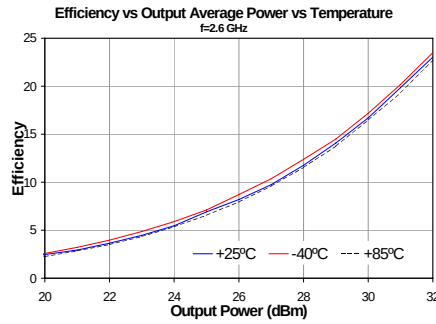
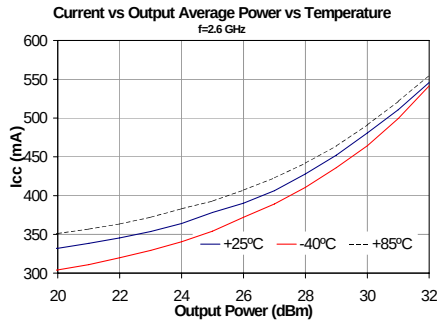
802.16-2004 O-FDMA, 64QAM-1/2, 1024-FFT, 20 symbols and 30 subchannels. 9.5 dB PAR @ 0.01%, 5 MHz Carrier BW





AP561

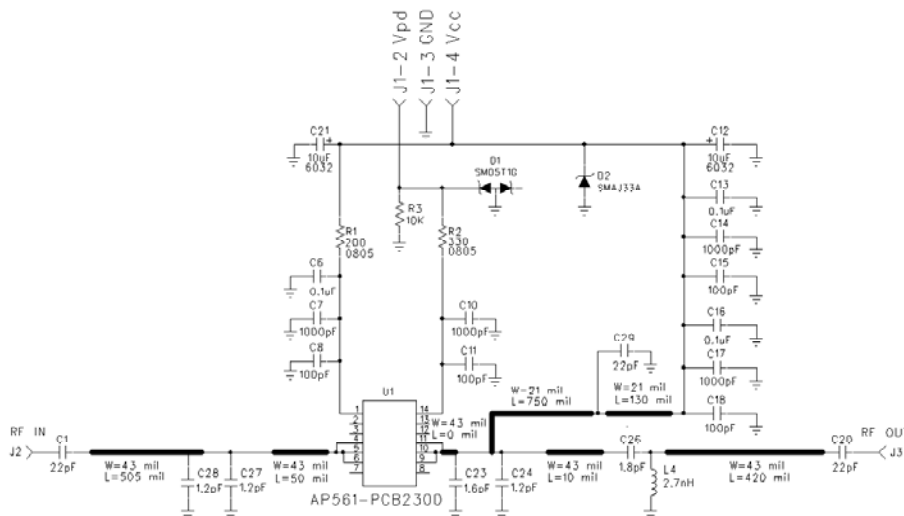
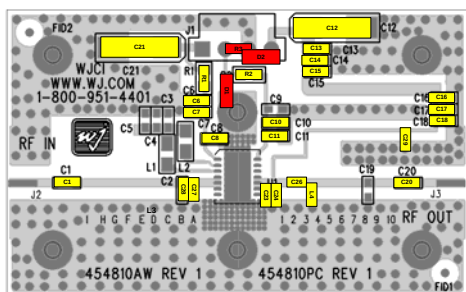
2.3-2.9 GHz WiMAX 8W Power Amplifier



2.3-2.9 GHz Application Circuit

Typical O-FDMA Performance at 25°C

Frequency (GHz)	2.3	2.6	2.9	Units
Channel Power	+30	+30	+30	dBm
Power Gain	13	12.7	13.2	dB
Input Return Loss	17	14	16	dB
Output Return Loss	3.3	4.0	5.9	dB
EVM	1.9	2.5	2.4	%
Operating Current, I _{cc}	630	640	570	mA
Collector Efficiency	13	12.7	14.3	%
Output P _{1dB}	40	39	39	dBm
Quiescent Current, I _{cq}	300			mA
V _{pd}	+5			V
V _{cc}	+12			V



Notes:

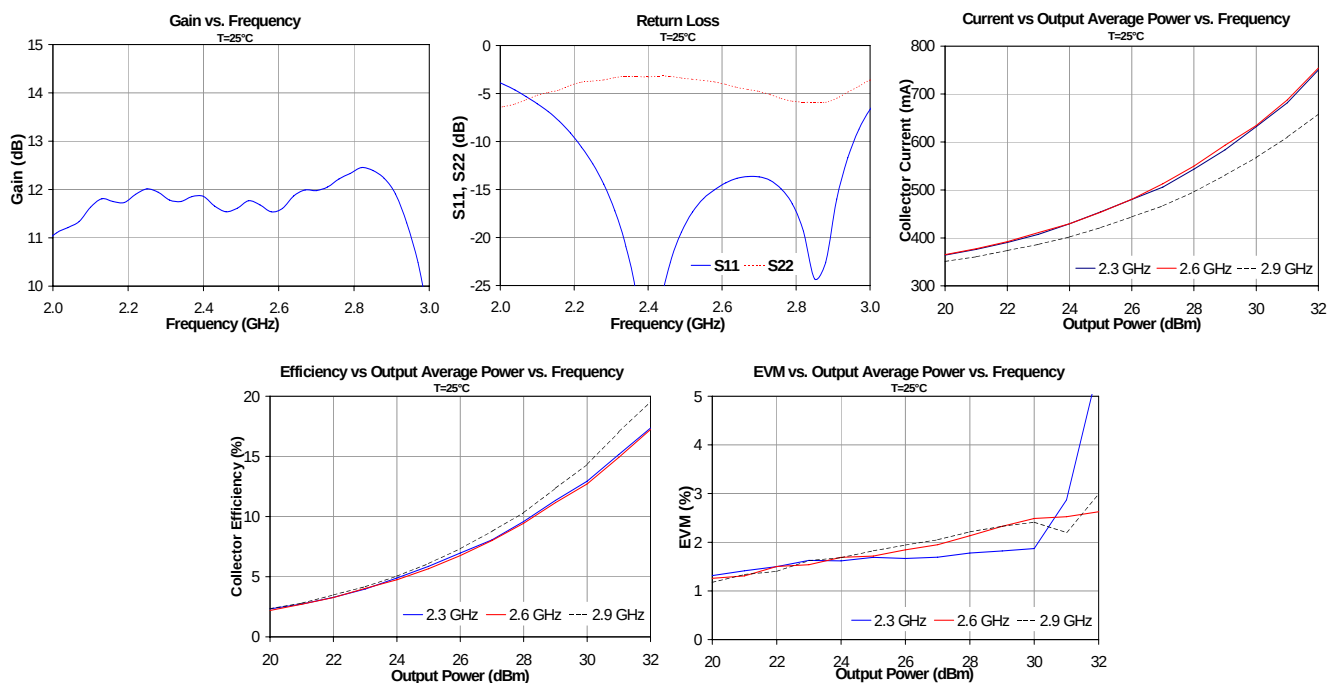
The primary RF microstrip line is 50 Ω.

Components shown on the silkscreen but not on the schematic are not used.

1. The edge of C26 is placed 10mil from C24.
2. The edge of L4 is placed right next to C26.
3. The edge of C23 is placed at 0mil from AP561 RFout pin.
4. The edge of C24 is placed right next to C23.
5. The center of C27 is placed at 50mil from AP561 RF in pin.
6. The edge of C28 is placed right next to C27.

2.3-2.9 GHz Application Circuit Performance Plots

802.16-2004 O-FDMA, 64QAM-1/2, 1024-FFT, 20 symbols and 30 subchannels. 9.5 dB PAR @ 0.01%, 5 MHz Carrier BW



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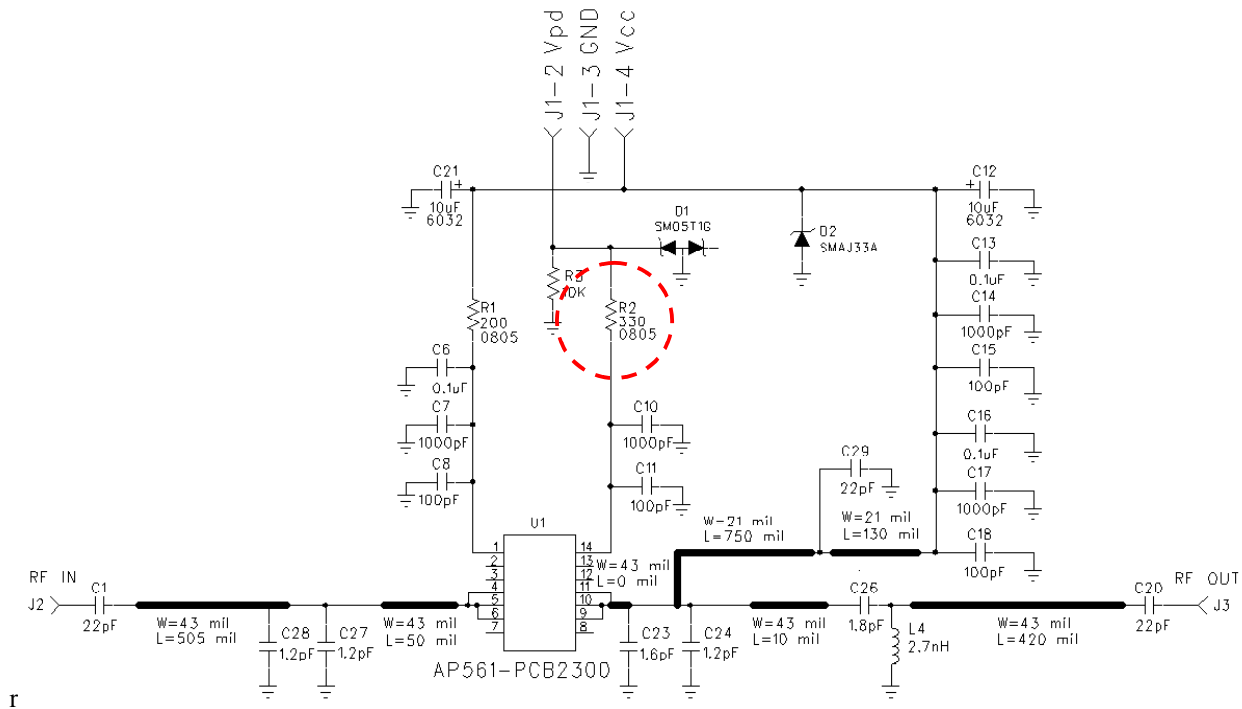
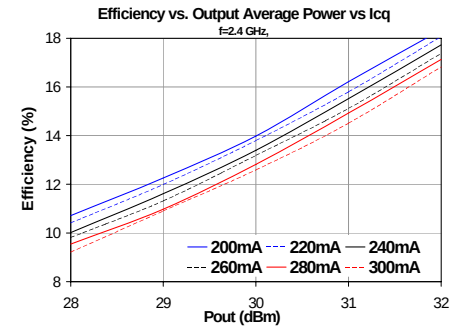
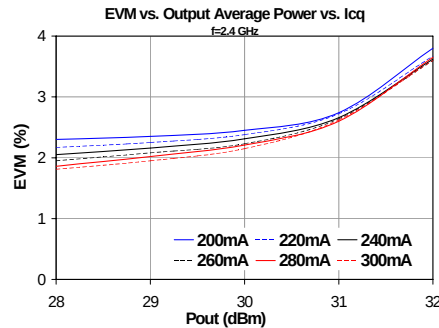


2.3 – 2.9 GHz Application Note: Changing I_{CQ} Biasing Configurations

The AP561 can be configured to operate with lower bias current by varying the bias-adjust resistor R2. (Table 1) The recommended circuit configurations shown previously in this datasheet have the device operating with a 300 mA as the quiescent current (I_{CQ}). This biasing level represents a tradeoff in terms of EVM and efficiency. Lowering I_{CQ} will improve upon the efficiency of the device, but degrade the EVM performance. Measured data shown in the plots below represents the AP561 measured and configured for 2.4 GHz applications. It is expected that variation of the bias current for other frequency applications will produce similar performance results.

Table 1 : Reduced Current Operation

I_{CQ} (mA)	R2 (Ω)	V_{PD} (V)	I_{REF} (V)
300	330	5	2.85
280	336	5	2.81
260	240	5	2.78
240	343	5	2.76
220	348	5	2.73
200	351	5	2.71





Parameter Measurement Information

Switching Speed Test

Test Conditions:

$V_{CC} = +12V$ at $25^{\circ}C$

Output Power = +30dBm @ 2.5 GHz

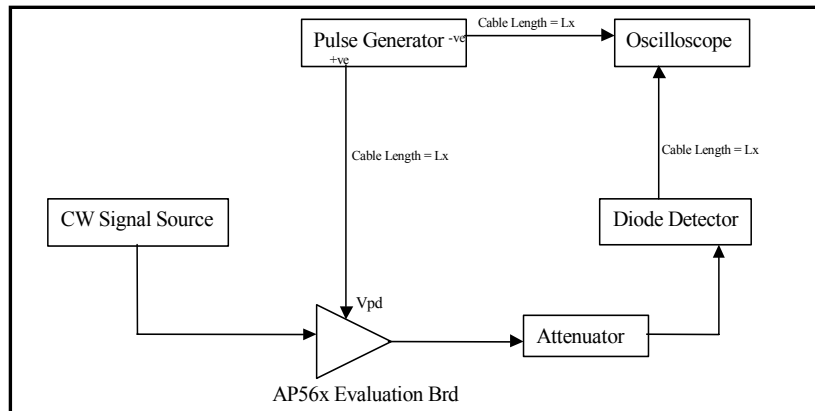
Rep Rate = 1 KHz, 50% duty cycle

V_{pd} amplitude = +5V

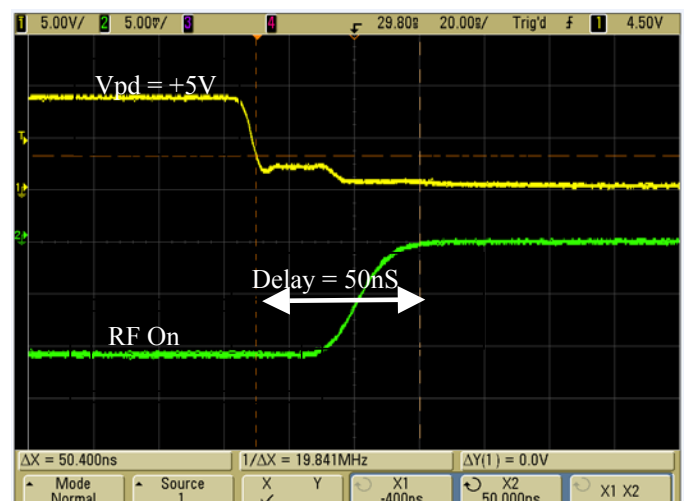
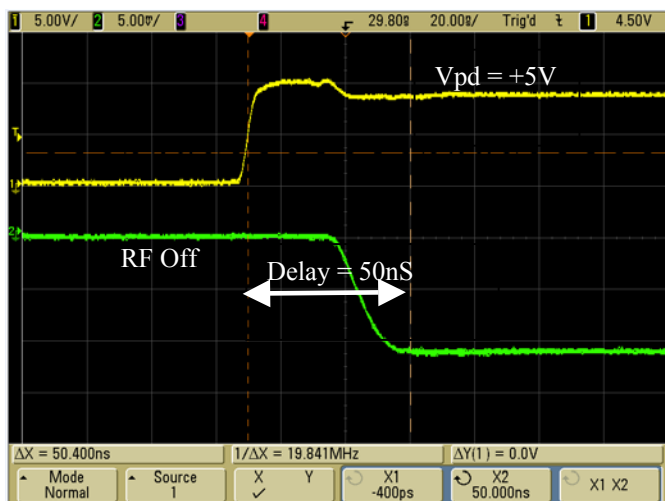
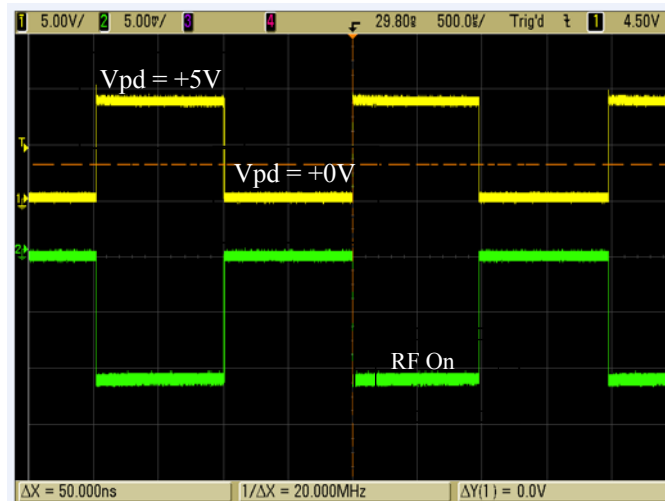
$R_2 = 200\ \Omega$, $C_9 = 12pF$

(C10, C11 removed for best switching performance)

Xtal Detector Voltage = 15mV (square law)



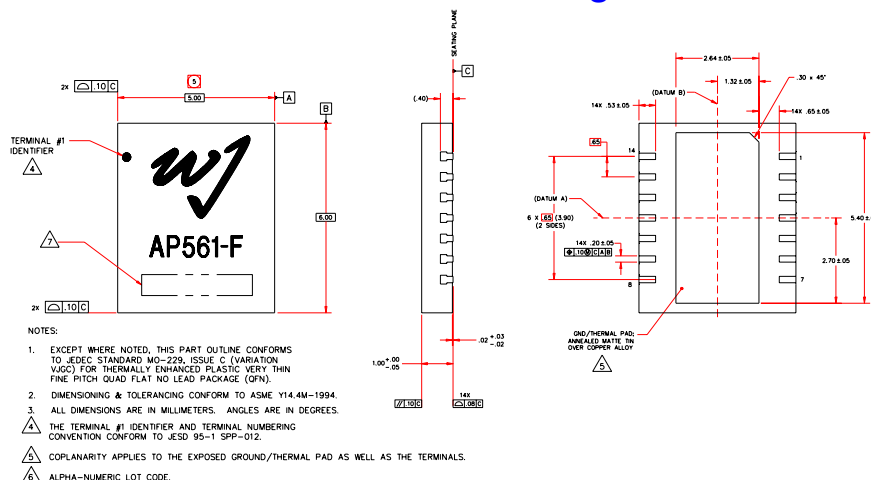
Test Result Waveforms:



Mechanical Information

This package is lead-free/Green/RoHS-compliant. The plating material on the pins is annealed matte tin over copper. It is compatible with both lead-free (maximum 260 °C reflow temperature) and leaded (maximum 245 °C reflow temperature) soldering processes.

Outline Drawing

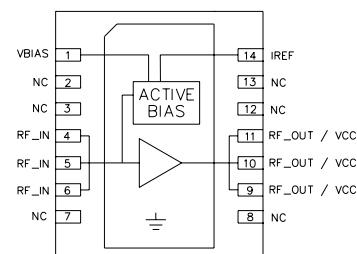


Product Marking

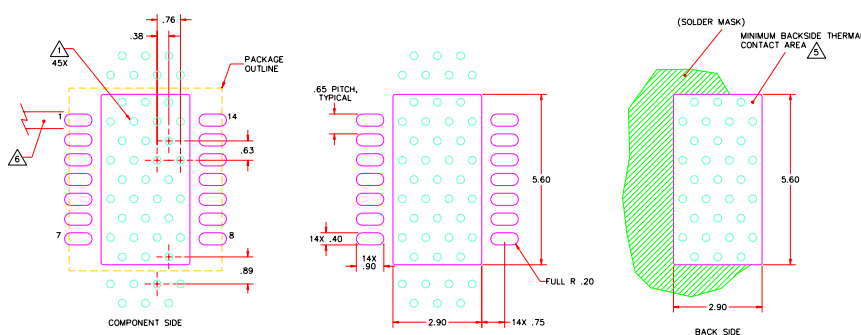
The component will be laser marked with a "AP561-F" product label with an alphanumeric lot code on the top surface of the package.

Tape and reel specifications for this part will be located on the website in the "Application Notes" section.

Functional Pin Layout



Mounting Configuration / Land Pattern



Pin	Function
1	VBIAS
2, 3, 7, 8, 12, 13	N/C
4, 5, 6	RF IN
9, 10, 11	RF Output / Vcc
14	IREF
Backside paddle	GND

MSL / ESD Rating



Caution! ESD sensitive device.

ESD Rating: Class 1A
Value: Passes $\geq 250V$ to $<500V$
Test: Human Body Model (HBM)
Standard: JEDEC Standard JESD22-A114

ESD Rating: Class IV
Value: Passes $\geq 1000V$ to $<2000V$
Test: Charged Device Model (CDM)
Standard: JEDEC Standard JESD22-C101

MSL Rating: Level 3 at $+260^{\circ}C$ convection reflow
Standard: JEDEC Standard J-STD-020